2-Input NOR Gate / CMOS Logic Level Shifter with LSTTL-Compatible Inputs

The MC74VHC1GT02 is a single gate 2–input NOR fabricated with silicon gate CMOS technology. It achieves high speed operation similar to equivalent Bipolar Schottky TTL while maintaining CMOS low power dissipation.

The internal circuit is composed of three stages, including a buffer output which provides high noise immunity and stable output.

The device input is compatible with TTL-type input thresholds and the output has a full 5V CMOS level output swing. The input protection circuitry on this device allows overvoltage tolerance on the input, allowing the device to be used as a logic-level translator from 3.0V CMOS logic to 5.0V CMOS Logic or from 1.8V CMOS logic to 3.0V CMOS Logic while operating at the high-voltage power supply.

The MC74VHC1GT02 input structure provides protection when voltages up to 7V are applied, regardless of the supply voltage. This allows the MC74VHC1GT02 to be used to interface 5V circuits to 3V circuits. The output structures also provide protection when $V_{CC} = 0V$. These input and output structures help prevent device destruction caused by supply voltage – input/output voltage mismatch, battery backup, hot insertion, etc.

- High Speed: $t_{PD} = 4.7$ ns (Typ) at $V_{CC} = 5V$
- Low Power Dissipation: $I_{CC} = 2\mu A$ (Max) at $T_A = 25^{\circ}C$
- TTL–Compatible Inputs: $V_{IL} = 0.8V$; $V_{IH} = 2.0V$
- CMOS–Compatible Outputs: $V_{OH} > 0.8V_{CC}$; $V_{OL} < 0.1V_{CC}$ @Load
- Power Down Protection Provided on Inputs and Outputs
- Balanced Propagation Delays
- Pin and Function Compatible with Other Standard Logic Families
- Latchup Performance Exceeds 300mA
- ESD Performance: HBM > 2000V

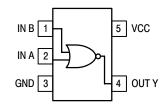
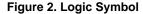


Figure 1. 5-Lead SOT-353 Pinout (Top View)



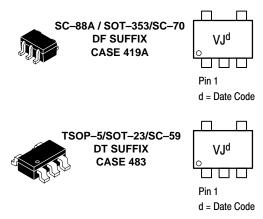




ON Semiconductor

http://onsemi.com

MARKING DIAGRAMS



PIN ASSIGNMENT							
1	IN B						
2	IN A						
3	GND						
4	OUT Y						
5	VCC						

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

FUNCTION TABLE

Inp	uts	Output
Α	В	Y
L	L	Н
L	Н	L
Н	L	L
Н	Н	L

MAXIMUM RATINGS*

Characteristics	Symbol	Value	Unit
DC Supply Voltage	V _{CC}	-0.5 to +7.0	V
DC Input Voltage	V _{IN}	-0.5 to +7.0	V
DC Output Voltage V _{CC} = 0 High or Low State	V _{OUT}	−0.5 to 7.0 −0.5 to V _{CC} + 0.5	V
Input Diode Current	I _{IK}	-20	mA
Output Diode Current $(V_{OUT} < GND; V_{OUT} > V_{CC})$	I _{OK}	+20	mA
DC Output Current, per Pin	lout	+25	mA
DC Supply Current, V _{CC} and GND	I _{CC}	+50	mA
Power dissipation in still air, SC-88A †	PD	200	mW
Lead temperature, 1 mm from case for 10 s	TL	260	°C
Storage temperature	T _{stg}	-65 to +150	°C

* Maximum Ratings are those values beyond which damage to the device may occur. Exposure to these conditions or conditions beyond those indicated may adversely affect device reliability. Functional operation under absolute-maximum-rated conditions is not implied. Functional operation should be restricted to the Recommended Operating Conditions.

†Derating — SC-88A Package: -5 mW/°C from 65° to 125°C

RECOMMENDED OPERATING CONDITIONS

Characteristics		Symbol	Min	Max	Unit
DC Supply Voltage		V _{CC}	3.0	5.5	V
DC Input Voltage		V _{IN}	0.0	5.5	V
DC Output Voltage V _{CC} = 0 High or Low S	State	V _{OUT}	0.0 0.0	5.5 V _{CC}	V
Operating Temperature Range		T _A	-55	+125	°C
Input Rise and Fall Time $V_{CC} = 3.3V \pm V_{CC} = 5.0V \pm 100$		t _r , t _f	0 0	100 20	ns/V

The θ_{JA} of the package is equal to 1/Derating. Higher junction temperatures may affect the expected lifetime of the device per the table and figure below.

DEVICE JUNCTION TEMPERATURE VERSUS TIME TO 0.1% BOND FAILURES

Junction Temperature °C	Time, Hours	Time, Years
80	1,032,200	117.8
90	419,300	47.9
100	178,700	20.4
110	79,600	9.4
120	37,000	4.2
130	17,800	2.0
140	8,900	1.0

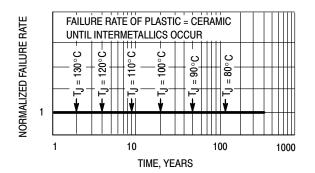


Figure 3. Failure Rate vs. Time Junction Temperature

			V _{CC}	ר	Γ _A = 25°0	C	T _A ≤	85°C	TA ≤ <i>'</i>	125°C	
Symbol	Parameter	Test Conditions	(V)	Min	Тур	Мах	Min	Мах	Min	Max	Unit
V _{IH}	Minimum High–Level Input Voltage		3.0 4.5 5.5	1.4 2.0 2.0			1.4 2.0 2.0		1.4 2.0 2.0		V
V _{IL}	Maximum Low–Level Input Voltage		3.0 4.5 5.5			0.53 0.8 0.8		0.53 0.8 0.8		0.53 0.8 0.8	V
V _{OH}	Minimum High–Level Output Voltage	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OH} = -50 \mu A$	3.0 4.5	2.9 4.4	3.0 4.5		2.9 4.4		2.9 4.4		V
	$V_{IN} = V_{IH} \text{ or } V_{IL}$		3.0 4.5	2.58 3.94			2.48 3.80		2.34 3.66		V
V _{OL}	Maximum Low–Level Output Voltage	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OL} = 50 \mu A$	3.0 4.5		0.0 0.0	0.1 0.1		0.1 0.1		0.1 0.1	V
	$V_{IN} = V_{IH} \text{ or } V_{IL}$	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OL} = 4mA$ $I_{OL} = 8mA$	3.0 4.5			0.36 0.36		0.44 0.44		0.52 0.52	V
I _{IN}	Maximum Input Leakage Current	$V_{IN} = 5.5V \text{ or GND}$	0 to 5.5			±0.1		±1.0		±1.0	μA
I _{CC}	Maximum Quiescent Supply Current	$V_{IN} = V_{CC}$ or GND	5.5			2.0		20		40	μA
I _{CCT}	Quiescent Supply Current	Per Input: $V_{IN} = 3.4V$ Other Input: V_{CC} or GND	5.5			1.35		1.50		1.65	mA
I _{OPD}	Output Leakage Current	V _{OUT} = 5.5V	0.0			0.5		5.0		10	μA

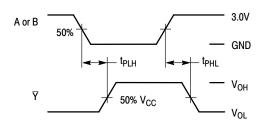
DC ELECTRICAL CHARACTERISTICS

AC ELECTRICAL CHARACTERISTICS ($C_{load} = 50 \text{ pF}$, Input $t_r = t_f = 3.0 \text{ns}$)

					T _A = 25°C	C	TA ≤	85°C	TA ≤ <i>'</i>	125°C	
Symbol	Parameter	Test Condi	itions	Min	Тур	Max	Min	Max	Min	Max	Unit
t _{PLH} , t _{PHL}	Maximum Propogation Delay,	$V_{CC} = 3.0 \pm 0.3 V$	C _L = 15 pF C _L = 50 pF		4.5 5.8	10.0 13.5		11.0 15.0		13.0 17.5	ns
	Input A or B to Y	$V_{CC} = 5.0 \pm 0.5 V$	C _L = 15 pF C _L = 50 pF		3.0 3.8	6.7 7.7		7.5 8.5		8.5 9.5	
C _{IN}	Maximum Input Capacitance				5.5	10		10		10	pF
						Ту	vpical @	25°C, V	_{CC} = 5.0	v	
C _{PD}	Power Dissipation Cap	acitance (Note 1.)						11			pF

 C_{PD} Power Dissipation Capacitance (Note 1.)

1. C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: $I_{CC(OPR)} = C_{PD} \bullet V_{CC} \bullet f_{in} + I_{CC}$. C_{PD} is used to determine the no-load dynamic power consumption; $P_D = C_{PD} \bullet V_{CC}^2 \bullet f_{in} + I_{CC} \bullet V_{CC}$.



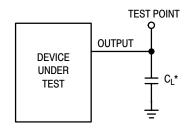
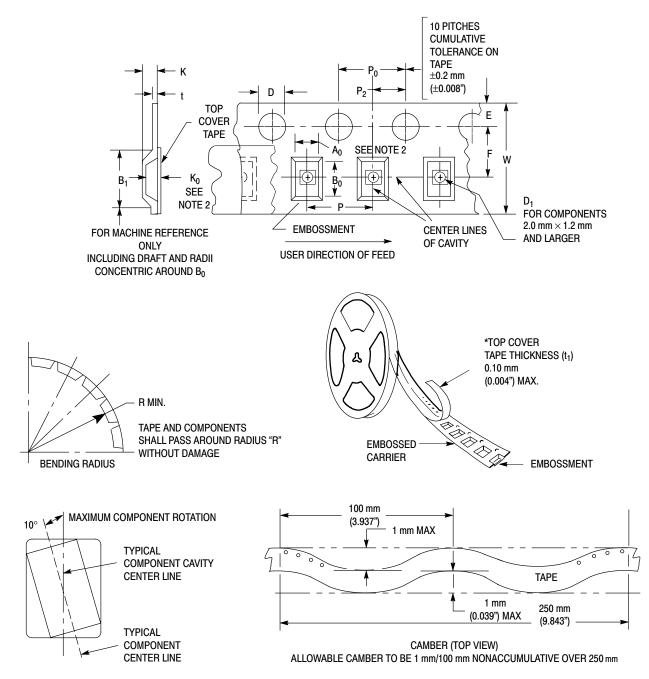


Figure 4. Switching Waveforms

*Includes all probe and jig capacitance Figure 5. Test Circuit

DEVICE ORDERING INFORMATION Device Nomenclature Temp Tape & Package Type (Name/SOT#/ Range Identifier Circuit Device Package Reel Tape and Device Indicator Function Suffix Suffix **Order Number** Technology Common Name) Reel Size SC-88A / SOT-353 178 mm (7") MC74VHC1GT02DFT2 MC 74 VHC1G T02 DF T2 / SC-70 3000 Unit SC-88A / SOT-353 330 mm (13") 10000 Unit DF / SC-70 MC74VHC1GT02DFT4 MC 74 VHC1G T02 Τ4 TSOPS / SOT-23 178 mm (7") MC74VHC1GT02DTT1 MC 74 VHC1G T02 DT T1 / SC-59 3000 Unit TSOPS / SOT-23 330 mm (13") 10000 Ùnit MC VHC1G DT / SC-59 MC74VHC1GT02DTT3 74 T02 Т3

http://onsemi.com 4





Tape Size	B ₁ Max	D	D ₁	Е	F	к	Р	P ₀	P ₂	R	т	w
8 mm	4.35 mm (0.171")	1.5 +0.1/ -0.0 mm (0.059 +0.004/ -0.0")	1.0 mm Min (0.039")	1.75 ±0.1 mm (0.069 ±0.004")	3.5 ±0.5 mm (1.38 ±0.002")	2.4 mm (0.094")	4.0 ±0.10 mm (0.157 ±0.004")	4.0 ±0.1 mm (0.156 ±0.004")	2.0 ±0.1 mm (0.079 ±0.002")	25 mm (0.98")	0.3 ±0.05 mm (0.01 +0.0038/ -0.0002")	8.0 ±0.3 mm (0.315 ±0.012")

EMBOSSED	CARRIER	DIMENSIONS	(See Note	s 1	and 2)
LINDOOOLD	OANNEN	DIMILINGIONO		5 1	

1. Metric Dimensions Govern-English are in parentheses for reference only.

2. A₀, B₀, and K₀ are determined by component size. The clearance between the components and the cavity must be within 0.05 mm min to 0.50 mm max. The component cannot rotate more than 10° within the determined cavity

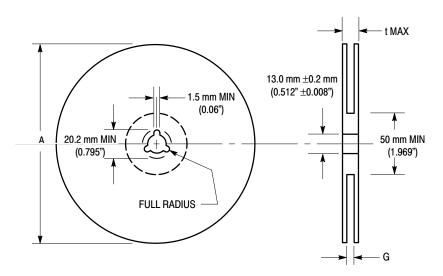
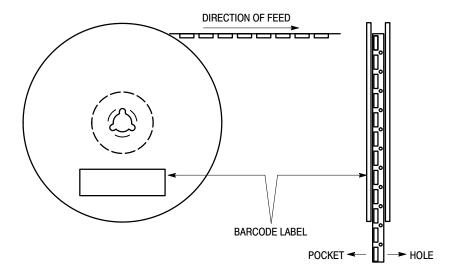


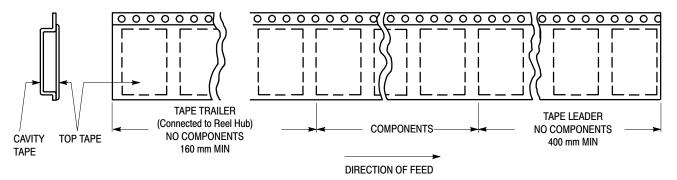
Figure 7. Reel Dimensions

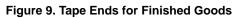
REEL DIMENSIONS

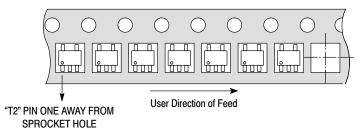
Tape Size	T&R Suffix	A Max	G	t Max
8 mm	T1, T2	178 mm (7")	8.4 mm, +1.5 mm, −0.0 (0.33" + 0.059", −0.00)	14.4 mm (0.56")
8 mm	T3, T4	330 mm (13")	8.4 mm, +1.5 mm, -0.0 (0.33" + 0.059", -0.00)	14.4 mm (0.56")

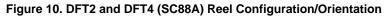












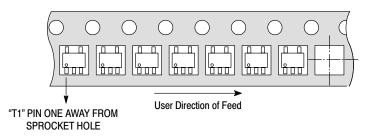
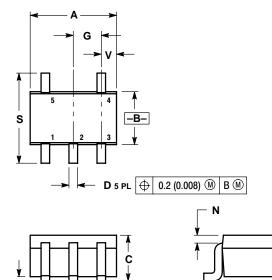


Figure 11. DTT1 and DTT3 (TSOP5) Reel ConfigurationOrientation

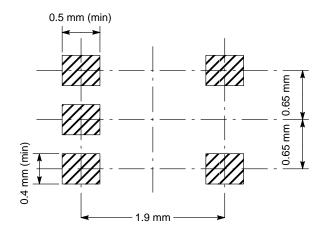
SC-88A / SOT-353 / SC-70 DF SUFFIX 5-LEAD PACKAGE CASE 419A-01 ISSUE B



— н

NOT	ES:
1.	DIMENSIONING AND TOLERANCING PER ANSI
	Y14.5M, 1982.
2.	CONTROLLING DIMENSION: MM.

	INC	HES	MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.071	0.087	1.80	2.20
В	0.045	0.053	1.15	1.35
С	0.031	0.043	0.80	1.10
D	0.004	0.012	0.10	0.30
G	0.026	BSC	0.65	BSC
Н		0.004		0.10
ſ	0.004	0.010	0.10	0.25
Κ	0.004	0.012	0.10	0.30
Ν	0.008 REF		0.20	REF
S	0.079	0.087	2.00	2.20
٧	0.012	0.016	0.30	0.40



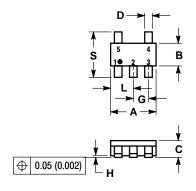
Κ·

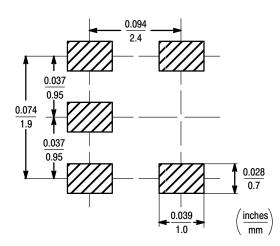
TSOP-5 / SOT-23 / SC-59 DT SUFFIX 5-LEAD PACKAGE CASE 483-01 ISSUE A

J

NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: MILLIMETER. 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	2.90	3.10	0.1142	0.1220
В	1.30	1.70	0.0512	0.0669
С	0.90	1.10	0.0354	0.0433
D	0.25	0.50	0.0098	0.0197
G	0.85	1.00	0.0335	0.0413
н	0.013	0.100	0.0005	0.0040
J	0.10	0.26	0.0040	0.0102
Κ	0.20	0.60	0.0079	0.0236
L	1.25	1.55	0.0493	0.0610
М	0 °	10 °	0°	10 °
S	2.50	3.00	0.0985	0.1181





<u>Notes</u>

<u>Notes</u>

ON Semiconductor and without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer.

PUBLICATION ORDERING INFORMATION

NORTH AMERICA Literature Fulfillment:

Literature Distribution Center for ON Semiconductor P.O. Box 5163, Denver, Colorado 80217 USA Phone: 303–675–2175 or 800–344–3860 Toll Free USA/Canada Fax: 303–675–2176 or 800–344–3867 Toll Free USA/Canada Email: ONlit@hibbertco.com Fax Response Line: 303–675–2167 or 800–344–3810 Toll Free USA/Canada

N. American Technical Support: 800–282–9855 Toll Free USA/Canada

EUROPE: LDC for ON Semiconductor – European Support

- German
 Phone: (+1) 303–308–7140 (Mon–Fri 2:30pm to 7:00pm CET)

 Email:
 ONlit–german@hibbertco.com

 French
 Phone: (+1) 303–308–7141 (Mon–Fri 2:00pm to 7:00pm CET)
- Email: ONlit-french@hibbertco.com
- English Phone: (+1) 303–308–7142 (Mon–Fri 12:00pm to 5:00pm GMT) Email: ONlit@hibbertco.com

EUROPEAN TOLL-FREE ACCESS*: 00-800-4422-3781 *Available from Germany, France, Italy, UK

CENTRAL/SOUTH AMERICA:

Spanish Phone: 303–308–7143 (Mon–Fri 8:00am to 5:00pm MST) Email: ONlit–spanish@hibbertco.com

ASIA/PACIFIC: LDC for ON Semiconductor – Asia Support Phone: 303–675–2121 (Tue–Fri 9:00am to 1:00pm, Hong Kong Time) Toll Free from Hong Kong & Singapore: 001–800–4422–3781 Email: ONlit–asia@hibbertco.com

JAPAN: ON Semiconductor, Japan Customer Focus Center 4–32–1 Nishi–Gotanda, Shinagawa–ku, Tokyo, Japan 141–0031 Phone: 81–3–5740–2745 Email: r14525@onsemi.com

ON Semiconductor Website: http://onsemi.com

For additional information, please contact your local Sales Representative.